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A Digitally Enhanced 1.8-V 15-b 40-Msample/s CMOS Pipelined ADC

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- Conventional PADC Example
- Digitally Enhanced PADC Prototype
- System-Level Design Details
- Circuit-Level Design Details
- Measured Results
- Conclusion













































Process, Layout and Packaging Overview

• Process

- 0.18 μm CMOS
- MiM capacitors, deep Nwells, thick-oxide devices, low- $V_{\rm T}$ devices
- Layout
 - Deep Nwells and multiple supply domains
 - No special attention to capacitor matching
 - ESD protection circuitry on all pads
- Packaging
 - 56-pin QFN package with exposed die paddle
 - Down-bonding of all grounds to exposed paddle
 - Double-bonding of critical supply pins









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Resolution	15 b
Sample Rate	40 MHz
Input Voltage Range	2.25 Vp-p differential
SFDR	90 dB
THD	88 dB
Peak SNR	72 dB
DNL	0.25 LSB
INL	1.5 LSB
SFDR Improvement with DNC and GEC enabled	> 20 dB
SNDR Improvement with DNC and GEC enabled	> 12 dB
Total Power	400 mW
Analog Power	343 mW (1.8 V)
Digital Power	51 mW (2.1 V)
Output Drivers Power	6 mW (1.8 V)
Technology	0.18µm 1P6M CMOS
Die Size	4mm x 5mm (including pads)
Package	56-Pin QFN with
	ground downbonding





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